L Number	Hits	Search Text	DB	Time stamp
-	34614	349/\$6	USPAT;	2003/11/24 08:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1645	((thin near3 film near "3" transistor) or (tft)) and	USPAT;	2004/03/09 08:53
		substrate and ((signal or gate or signaling) near3	US-PGPUB;	
		(line or electrode)) and array and insulat\$4 and	EPO; JPO;	
		dielectric and (pixel near4 electrode)	DERWENT;	
		,	IBM_TDB	
-	811	349/\$6 and (((thin near3 film near "3" transistor)	USPAT;	2003/11/24 08:45
		or (tft)) and substrate and ((signal or gate or	US-PGPUB;	
		signaling) near3 (line or electrode)) and array and	EPO; JPO;	
		insulat\$4 and dielectric and (pixel near4	DERWENT;	
		electrode))	IBM_TDB	
-	113819	silicon near3 nitride	USPAT;	2004/03/09 09:22
		Sincon near o menae	US-PGPUB;	2004/03/03/03/03.22
			EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
_	1380	((thin near3 film near "3" transistor) or (tft)) and	-	2002/11/24 00:46
	1300	substrate and ((signal or data or signaling) near3	USPAT;	2003/11/24 08:46
			US-PGPUB;	
1		(line or electrode)) and array and insulat\$4 and	EPO; JPO;	
		dielectric and (pixel near4 electrode)	DERWENT;	
	1700	(/thin noon) film noon) turnsistan) on (tft) and	IBM_TDB	2004/20/20 20 20
-	1708	((thin near3 film near3 transistor) or (tft)) and	USPAT;	2004/03/09 09:20
		substrate and ((signal or gate or signaling) near3	US-PGPUB;	
		(line or electrode)) and array and insulat\$4 and	EPO; JPO;	
		dielectric and (pixel near4 electrode)	DERWENT;	
	4700	(4)	IBM_TDB	
-	1728	((thin near3 film near3 transistor) or (tft)) and	USPAT;	2004/03/09 09:20
		substrate and ((signal or gate or signaling or	US-PGPUB;	
		scan\$4 or data) near3 (line or electrode)) and	EPO; JPO;	
		array and insulat\$4 and dielectric and (pixel near4	DERWENT;	
		electrode)	IBM_TDB	
-	576	(((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 09:21
		array near8 substrate) and ((signal or gate or	US-PGPUB;	
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
		electrode)) and array and insulat\$4 and dielectric	DERWENT;	
		and (pixel near4 electrode)	IBM_TDB	
-	418	(((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 11:01
		array near8 substrate) and ((signal or gate or	US-PGPUB;	
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
		electrode)) and array and insulat\$4 and (dielectric	DERWENT;	
		near "6" constant) and (pixel near4 electrode) and	IBM_TDB	
		hole		
-	118878	silicon near3 nitride	USPAT;	2004/03/09 09:23
			US-PGPUB;	, ,
1			EPO; JPO;	
			DERWENT;	
	:		IBM_TDB	
-	295	((((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 09:23
		array near8 substrate) and ((signal or gate or	US-PGPUB;	, 55, 55 65.25
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
	İ	electrode)) and array and insulat\$4 and (dielectric	DERWENT;	
		near "6" constant) and (pixel near4 electrode) and	IBM_TDB	
		hole) and (silicon near3 nitride)	1011_100	
_	241750	(indium near3 (tin or zinc) near3 oxide) or ito or	USPAT;	2004/02/00 00:24
	241/30	izo		2004/03/09 09:24
		120	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			·	
-	236208	(indium adj (tin or zinc) adj oxide) or ito or izo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24
-	277	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and ((indium adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:24
-	4402	(tin or zinc) adj oxide) or ito or izo) ((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:25
-	203	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:25
-	790203	chrom\$4 or cr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:11
-	4230267	aluminum or al	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:12
-	150	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (chrom\$4 or cr) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:45
-	448074	(aluminum or al) molybdenum or mo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:46
-	96476	(chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:47
-	243803	((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:49

-	87	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)) and (((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:53
-	67	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:13
-	54	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
-	51	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and ((indium adj (tin or zinc) adj oxide) or ito or izo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
-	34	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:04
-	33	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05
-	1426	349/43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10
-	2218	349/42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05

	2070	0.0710		
-	3078	349/43 or 349/42	USPAT; US-PGPUB; EPO; JPO;	2004/03/09 11:06
			DERWENT;	
_	11	((((((thin near3 film near3 transistor) or (tft))	IBM_TDB USPAT;	2004/03/09 11:10
		near8 array near8 substrate) and ((signal or gate	US-PGPUB;	=====================================
		or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4	EPO; JPO; DERWENT;	
		and (dielectric near6 constant) and (pixel near4	IBM_TDB	
		electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj		
		oxide) or ito or izo) near10 (pixel adj electrode)))		
		and ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (349/43 or 349/42)		
-	358	349/51	USPAT;	2004/03/09 11:10
			US-PGPUB; EPO; JPO;	
			DERWENT;	
_	89	349/52	IBM_TDB USPAT;	2004/03/09 11:10
		3.3,32	US-PGPUB;	2004/03/03 11:10
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	3427	349/43 or 349/42 or 349/51 or 349/52	USPAT; US-PGPUB;	2004/03/09 11:11
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	11	(((((((thin near3 film near3 transistor) or (tft))	USPAT;	2004/03/09 11:11
		near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source)	US-PGPUB; EPO; JPO;	
		near3 (line or electrode)) and array and insulat\$4	DERWENT;	
		and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon	IBM_TDB	
		near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode)))		
		and ((chrom\$4 or cr) or (aluminum or al) or		
		(molybdenum or mo))) and (349/43 or 349/42 or 349/51 or 349/52)		
-	6754	insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:12
		nitride)	US-PGPUB; EPO; JPO;	
	:		DERWENT;	
-	90796	(gate or scan\$4) near8 ((chrom\$4 or cr) or	IBM_TDB USPAT;	2004/03/09 11:14
		(aluminum or al) or (molybdenum or mo))	US-PGPUB;	
			EPO; JPO; DERWENT;	
_	42185	((thin near3 film near3 transistor) or (tft)) and	IBM_TDB USPAT;	2004/03/09 11:14
	72103	substrate	US-PGPUB;	2004/03/09 11:14
			EPO; JPO; DERWENT;	
	705555		IBM_TDB	
-	706656	(drain or data or source or signal\$4) near3 (line or electrode)	USPAT; US-PGPUB;	2004/03/09 11:15
		•	EPO; JPO;	
			DERWENT; IBM_TDB	

-	718	(insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	USPAT; US-PGPUB;	2004/03/09 11:15
		cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft))	EPO; JPO; DERWENT;	
		and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))	IBM_TDB	
_	32786	passivation near3 (film or layer or plate or coat\$4)	USPAT;	2004/03/09 11:16
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	290	((insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:29
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	
		cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft))	EPO; JPO; DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
i		signal\$4) near3 (line or electrode))) and	_	
:		(passivation near3 (film or layer or plate or		
-	1799	coat\$4)) (passivation near3 (film or layer or plate or	USPAT;	2004/03/09 11:31
		coat\$4)) same ((chemical near3 vapor near3	US-PGPUB;	, ,
		deposit\$3) or pevcd)	EPO; JPO;	
			DERWENT; IBM_TDB	
-	21	((insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:17
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	
		cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft))	EPO; JPO;	
		and substrate) and ((drain or data or source or	DERWENT; IBM_TDB	
		signal\$4) near3 (line or electrode))) and		
		((passivation near3 (film or layer or plate or		
		coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd))		~
-	152	349/\$6 and (((insulat\$4 near8 (dielectric and	USPAT;	2004/03/09 11:18
		silicon near3 nitride)) and ((gate or scan\$4) near8	US-PGPUB;	
		((chrom\$4 or cr) or (aluminum or al) or	EPO; JPO;	
		(molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and	DERWENT; IBM_TDB	
		((drain or data or source or signal\$4) near3 (line		
		or electrode))) and (passivation near3 (film or		
_	6	layer or plate or coat\$4))) 349/\$6 and (((insulat\$4 near8 (dielectric and	USPAT;	2004/03/09 11:18
		silicon near3 nitride)) and ((gate or scan\$4) near8	US-PGPUB;	2007/03/03 11.10
		((chrom\$4 or cr) or (aluminum or al) or	EPO; JPO;	
		(molybdenum or mo))) and (((thin near3 film	DERWENT;	
		near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line	IBM_TDB	
		or electrode))) and ((passivation near3 (film or		
		layer or plate or coat\$4)) same ((chemical near3		
	138	vapor near3 deposit\$3) or pevcd))) (((insulat\$4 near8 (dialectric and cilicon near3	LICDAT.	7004/02/00 44-20
_	136	(((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	USPAT; US-PGPUB;	2004/03/09 11:30
		cr) or (aluminum or al) or (molybdenum or mo)))	EPO; JPO;	
		and (((thin near3 film near3 transistor) or (tft))	DERWENT;	
		and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and	IBM_TDB	
		(passivation near3 (film or layer or plate or		
		coat\$4))) and ((dielectric or permittiv\$4) near3		
		(constant or coefficient))		

-	74	((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	USPAT; US-PGPUB;	2004/03/09 11:30
		cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or	EPO; JPO; DERWENT; IBM_TDB	
		signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or		
	32	coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6	LICDAT.	2004/02/10 10:57
_	32	(((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)))	USPAT; US-PGPUB; EPO; JPO;	2004/03/10 10:57
		and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or	DERWENT; IBM_TDB	
		signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3		
		(constant or coefficient))) and 349/\$6) and ((chemical near3 vapor near3 deposit\$3) or pevcd)		
-	13656	second near3 ((gate or scan\$4) and insulat\$4)	USPAT; US-PGPUB;	2004/03/10 11:19
			EPO; JPO; DERWENT; IBM_TDB	
-	16	nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	USPAT; US-PGPUB;	2004/03/10 11:20
		cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or	EPO; JPO; DERWENT; IBM_TDB	
		data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer	1014_100	
		or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and (second near3 ((gate or scan\$4) and		
_	7610	insulat\$4)) (second near3 insulat\$4) same (nitride)	USPAT;	2004/03/10 11:20
			US-PGPUB; EPO; JPO; DERWENT;	, , , , , , , , , , , , , , , , , , , ,
-	8	(((((	IBM_TDB USPAT;	2004/03/10 11:21
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3	US-PGPUB; EPO; JPO; DERWENT;	
		transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer	IBM_TDB	
		or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and ((second near3 insulat\$4) same		
-	12	(nitride)) "a-si:c:o" or "a-si:o:f"	USPAT;	2004/03/10 11:26
			US-PGPUB; EPO; JPO; DERWENT;	
	3	("a-si:c:o" or "a-si:o:f") and 349/\$6	IBM_TDB USPAT;	2004/03/10 11:26
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	

_	302	tao\$2 near8 dielectric	USPAT;	2004/08/27 14:06
	302	tabyz nearo alercetre	US-PGPUB;	2004/00/27 14:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	(tao\$2 near8 dielectric) and 349/\$	USPAT:	2004/08/27 14:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1948	((first or lower) near3 (gate or scan\$4) near3	USPAT;	2004/08/27 14:41
		(insulat\$5)) near9 (sio or silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1976	((first or lower) near3 (gate or scan\$4) near3	USPAT;	2004/08/27 14:42
		(insulat\$5)) near9 (sio\$4 or silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	129	(((first or lower) many) (sets or send 1) many)	IBM_TDB	2004/00/27 44 42
_	129	(((first or lower) near3 (gate or scan\$4) near3	USPAT;	2004/08/27 14:42
		(insulat\$5)) near9 (sio\$4 or silicon)) and 349/\$	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
·		1	IBM_TDB	